



# GANB4R8-040CBA

40 V, 4.8 mOhm bi-directional Gallium Nitride (GaN) FET in a 2.1 mm x 2.1 mm Wafer Level Chip-Scale Package (WLCSP)

7 August 2024

Product data sheet

## 1. General description

The GANB4R8-040CBA is a 40 V, 4.8 m $\Omega$  bi-directional Gallium Nitride (GaN) High Electron-Mobility-Transistor (HEMT) in a Wafer Level Chip-Scale (WLCSP) package. It is a normally-off e-mode device offering superior performance.

## 2. Features and benefits

- Enhancement mode - normally-off power switch
- Bi-directional device
- Ultra high switching speed capability
- Ultra-low on-state resistance
- RoHS, Pb-free, REACH-compliant
- High efficiency and high power density
- Wafer Level Chip-Scale Package (WLCSP) 2.1 mm x 2.1 mm

## 3. Applications

- High-side load switch
- OVP protection in smart phone USB port
- Power switch circuits
- Stand-by power system

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DD</sub>	drain-drain voltage	-40 °C $\leq$ T <sub>j</sub> $\leq$ 125 °C	[1]	-	-	40	V
I <sub>D</sub>	drain current	V <sub>GD</sub> = 5 V; T <sub>mb</sub> = 25 °C	[2] [3]	-	-	20	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Fig. 1		-	-	13	W
T <sub>j</sub>	junction temperature			-40	-	125	°C
<b>Static characteristics</b>							
R <sub>DDon</sub>	drain-drain on-state resistance	V <sub>GD2</sub> = 5 V; I <sub>D1</sub> = 10 A; T <sub>j</sub> = 25 °C; see Fig. 9 and Fig. 10	[1]	-	4	4.8	m $\Omega$
		V <sub>GD2</sub> = 5 V; I <sub>D1</sub> = 10 A; T <sub>j</sub> = 125 °C; see Fig. 9 and Fig. 11	[1]	-	7	-	m $\Omega$

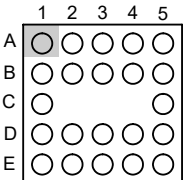
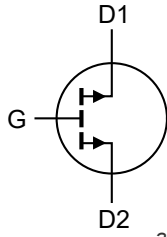
40 V, 4.8 mOhm bi-directional Gallium Nitride (GaN) FET in a 2.1 mm x 2.1 mm Wafer Level Chip-Scale Package (WLCSP)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 10\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 5\text{ V}$ ; $T_j = 25\text{ °C}$ ; see Fig. 12 and Fig. 13	[2]	-	15.8	-	nC

- [1] Parameters are understood to apply for either polarity of bias. For example,  $V_{DD}$  is the same whether D1 is the source and D2 is the drain or vice versa..
- [2] D1 and D2 are symetrical with respect to the gate, G. Either can take the function of source or drain. For datasheet parameters, the source is defined as the terminal, D1 or D2, which has lower potential in the test circuit. The drain is the terminal with the higher potential.
- [3] Limited by solder ball.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
A1-A5, D1-D5	D1	drain1	 Transparent top view WLCSP22_SOT8086	 aaa-037587
B1-B5, E1-E5	D2	drain2		
C5	G	gate		
C1	NC	not connected		

## 6. Ordering information

Table 3. Ordering information

Type number	Orderable part number, (Ordering code (12NC))	Package		
		Name	Description	Version
GANB4R8-040CBA	GANB4R8-040CBAZ (934667630341)	WLCSP22_SOT8086	WLCSP22, 2.1 x 2.1 mm	WLCSP22_SOT8086

## 7. Marking

Table 4. Marking codes

Type number	Marking code
GANB4R8-040CBA	4R8ACBA

## 8. Limiting values

Table 5. Limiting values

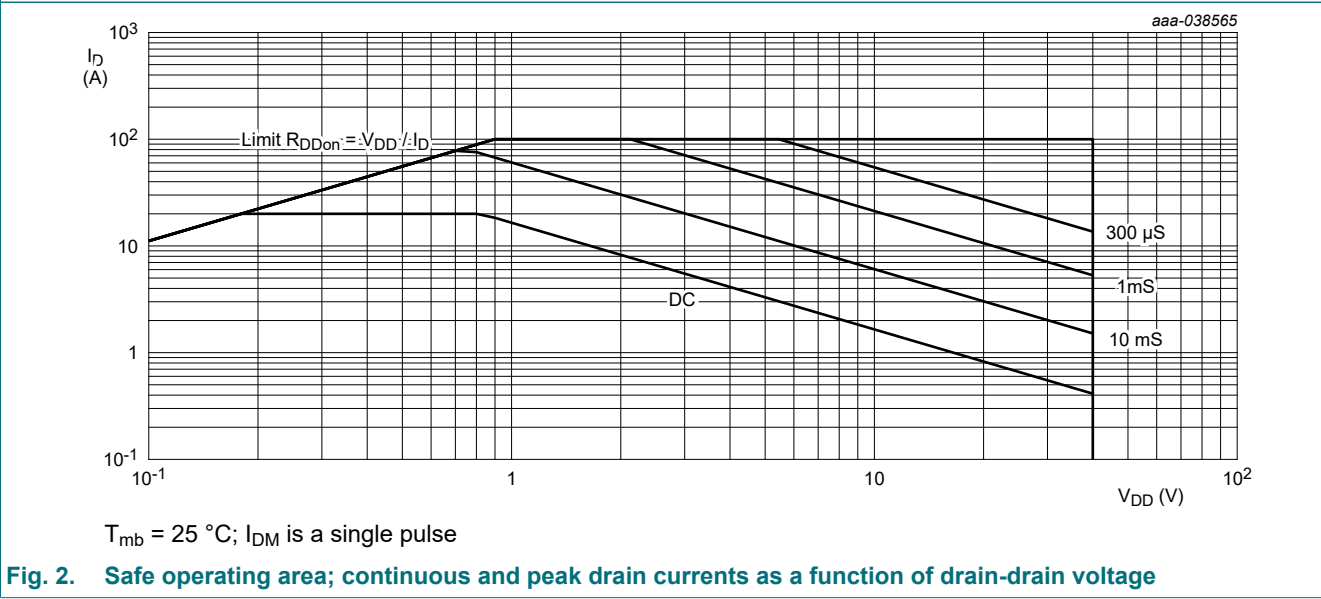
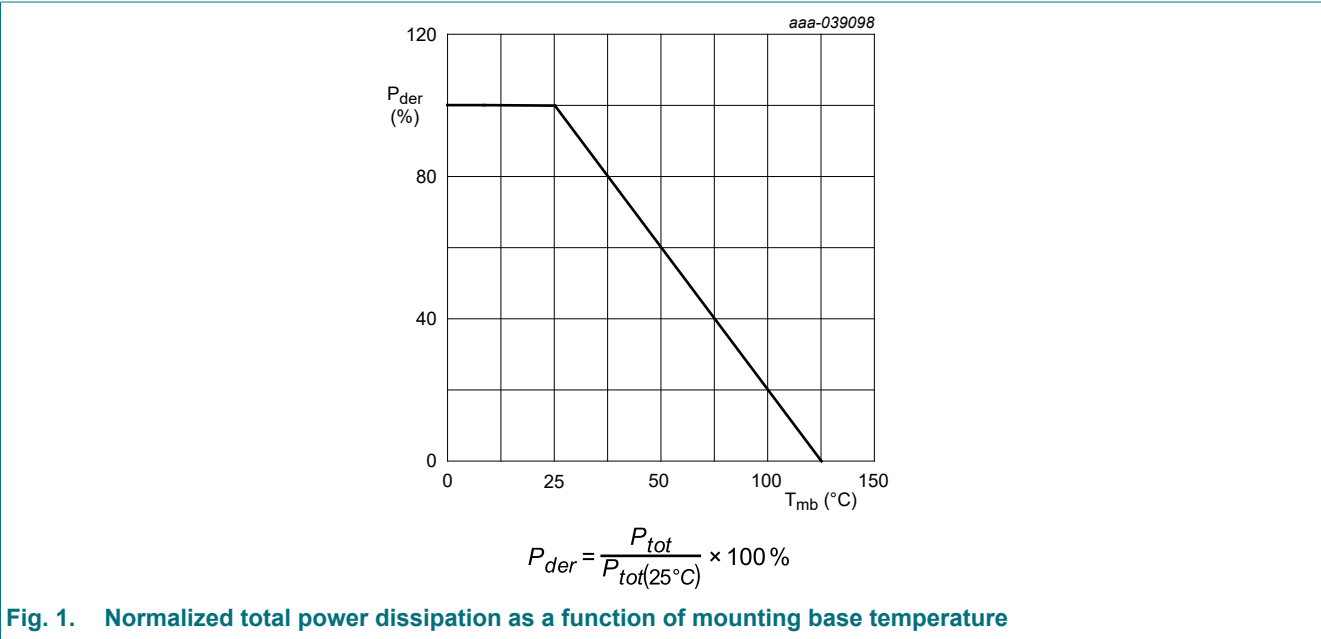
In accordance with the Absolute Maximum Rating System (IEC 60134).  $T_j = 25\text{ °C}$  unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DD}$	drain-drain voltage	$-40\text{ °C} \leq T_j \leq 125\text{ °C}$	[1]	-	40	V
$V_{DG}$	drain-gate voltage		[1]	-	40	V
$V_{GD}$	gate-drain voltage		[1]	-	6	V
$I_D$	drain current	$V_{GD} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$	[2] [3]	-	20	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 300\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see Fig. 2	[2] [3]	-	100	A

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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Fig. 1		-	13	W
T <sub>stg</sub>	storage temperature			-40	150	°C
T <sub>j</sub>	junction temperature			-40	125	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C

- [1] Parameters are understood to apply for either polarity of bias. For example, VDD is the same whether D1 is the source and D2 is the drain or vice versa.
- [2] D1 and D2 are symetrical with respect to the gate, G. Either can take the function of source or drain. For datasheet parameters, the source is defined as the terminal, D1 or D2, which has lower potential in the test circuit. The drain is the terminal with the higher potential.
- [3] Limited by solder ball.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case		[1]	-	-	12.6	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Fig. 3		-	-	7.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[2]	-	-	59.3	K/W

- [1] Thermal junction to top side of package.  
[2]  $R_{th(j-a)}$  is determined with the device mounted on one square inch of copper pad single layer 2 oz copper on FR4 board.

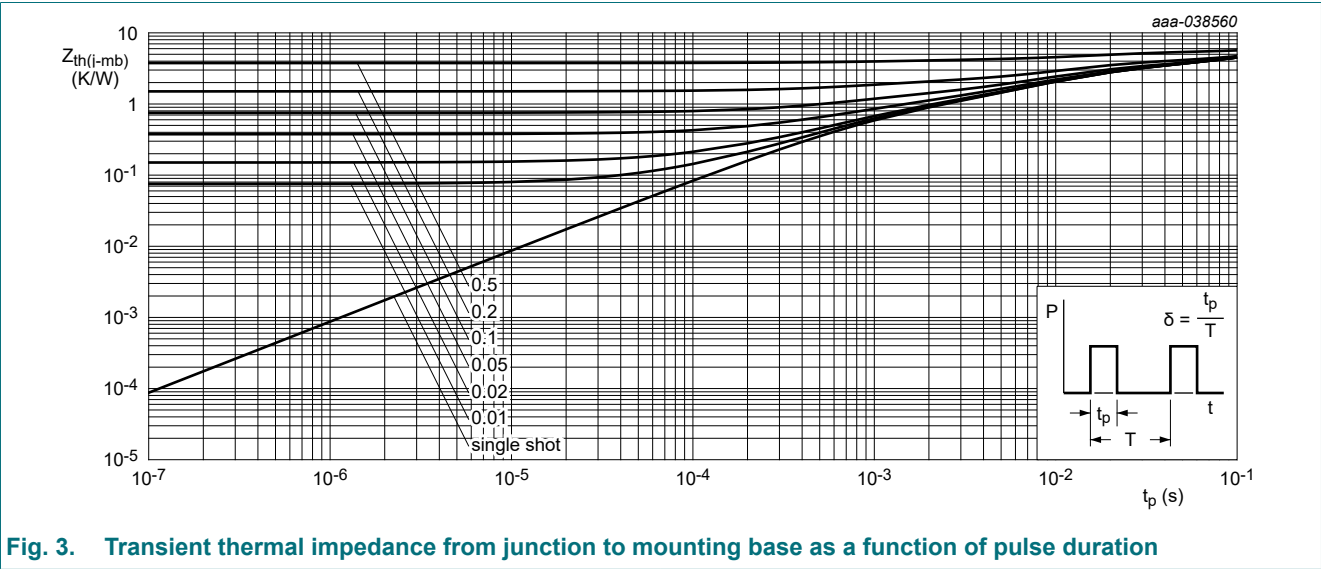


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
BV <sub>DD</sub> <sub>S</sub>	drain-drain breakdown voltage	I <sub>D1D2</sub> = 500 µA; V <sub>D2</sub> = V <sub>G</sub> = 0V; T <sub>j</sub> = 25 °C	[1]	40	-	-	V
V <sub>GD(th)</sub>	gate-drain threshold voltage	I <sub>D</sub> = 1 mA; V <sub>D1</sub> = 0 V; V <sub>D2</sub> = V <sub>G</sub> ; T <sub>j</sub> = 25 °C; see Fig. 8	[1]	0.8	1.35	2.4	V
		I <sub>D</sub> = 1 mA; V <sub>D1</sub> = 0 V; V <sub>D2</sub> = V <sub>G</sub> ; T <sub>j</sub> = 125 °C; see Fig. 8	[1]	-	1.1	-	V
I <sub>DD</sub> <sub>S</sub>	drain-drain leakage current	V <sub>DD</sub> = 40 V; V <sub>GD</sub> = 0 V; T <sub>j</sub> = 25 °C	[1]	-	1	20	µA
I <sub>GDS</sub>	gate-drain leakage current	V <sub>GD</sub> = 5 V; V <sub>DD</sub> = 0 V; T <sub>j</sub> = 85 °C	[1]	-	0.5	3	µA
		V <sub>GD</sub> = -5 V; V <sub>DD</sub> = 0 V; T <sub>j</sub> = 85 °C		-30	-	-	µA
		V <sub>GD</sub> = 6 V; V <sub>DD</sub> = 0 V; T <sub>j</sub> = 85 °C		-	5	30	µA
		V <sub>GD</sub> = -6 V; V <sub>DD</sub> = 0 V; T <sub>j</sub> = 85 °C		-40	-	-	µA
R <sub>DDon</sub>	drain-drain on-state resistance	V <sub>GD2</sub> = 5 V; I <sub>D1</sub> = 10 A; T <sub>j</sub> = 25 °C; see Fig. 9 and Fig. 10	[1]	-	4	4.8	mΩ
		V <sub>GD2</sub> = 5 V; I <sub>D1</sub> = 10 A; T <sub>j</sub> = 125 °C; see Fig. 9 and Fig. 11		-	7	-	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	[1]	-	4	-	Ω
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; see Fig. 12 and Fig. 13	[2]	-	15.8	-	nC
Q <sub>GS</sub>	gate-source charge			-	1.9	-	nC
Q <sub>GD</sub>	gate-drain charge			-	8.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see Fig. 14	[2]	-	887	-	pF
C <sub>oss</sub>	output capacitance			-	381	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	226	-	pF
Q <sub>oss</sub>	output charge	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see Fig. 7	[2][3]	-	12.2	-	nC

- [1] Parameters are understood to apply for either polarity of bias. For example, V<sub>DD</sub> is the same whether D1 is the source and D2 is the drain or vice versa.
- [2] D1 and D2 are symetrical with respect to the gate, G. Either can take the function of source or drain. For datasheet parameters, the source is defined as the terminal, D1 or D2, which has lower potential in the test circuit. The drain is the terminal with the higher potential.
- [3] Q<sub>r</sub> is not specified separately from Q<sub>oss</sub> for e-mode GaN FETs, since Q<sub>r</sub> = Q<sub>oss</sub> + Q<sub>D</sub>, and Q<sub>D</sub> = 0. (Q<sub>D</sub> is charge associated with diffusion of minority carriers. Since there is no body diode, no minority carriers in excess of Q<sub>oss</sub> have to be transferred for e-mode GaN FETs.)

40 V, 4.8 mOhm bi-directional Gallium Nitride (GaN) FET in a 2.1 mm x 2.1 mm Wafer Level Chip-Scale Package (WLCSP)

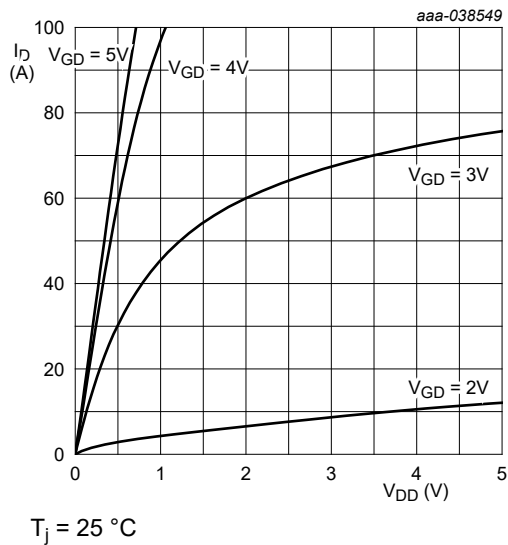


Fig. 4. Output characteristics; drain current as a function of drain-drain voltage; typical values

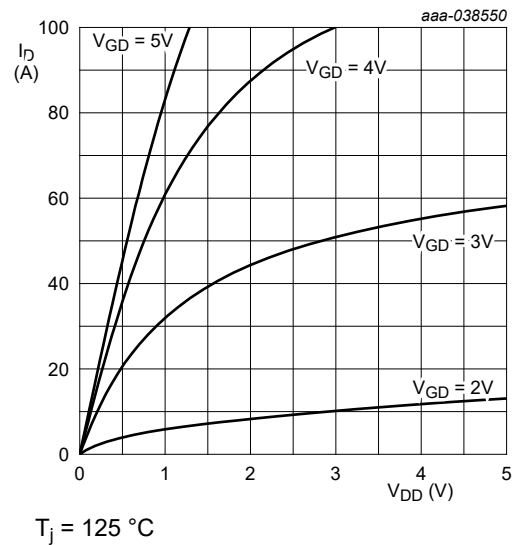


Fig. 5. Output characteristics; drain current as a function of drain-drain voltage; typical values

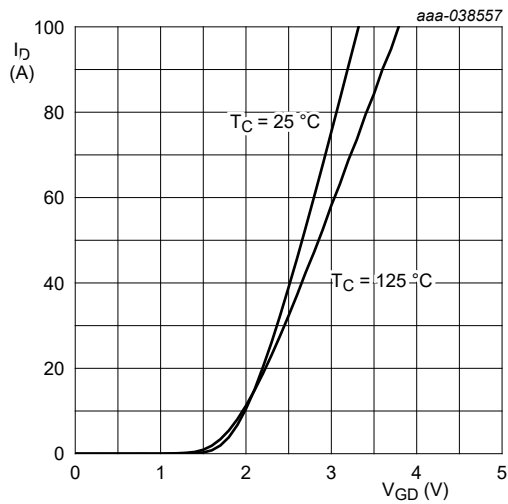


Fig. 6. Transfer characteristics; drain current as a function of gate-drain voltage; typical values

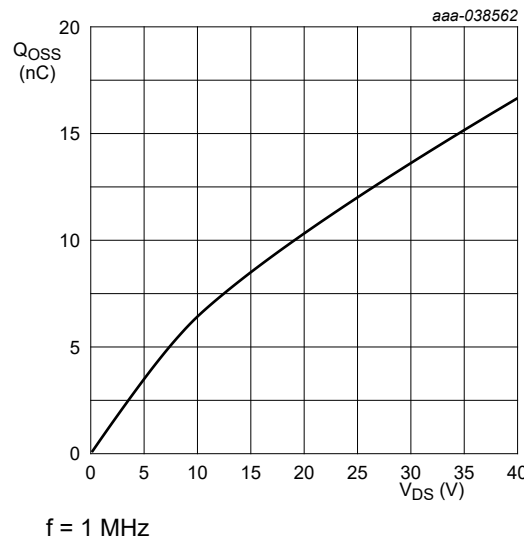
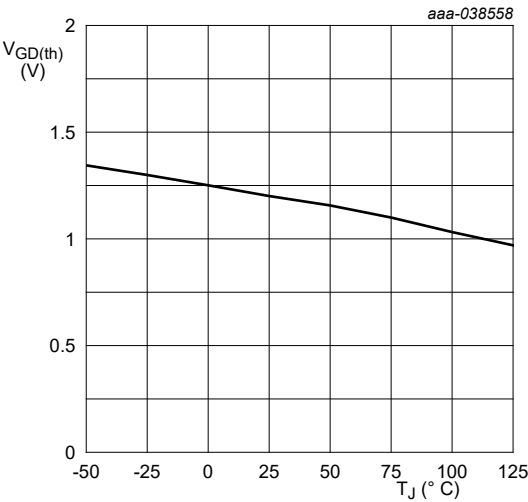


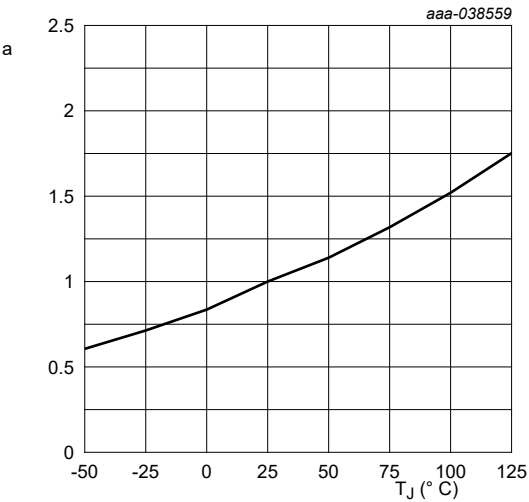
Fig. 7. Output charge as a function of drain-source voltage; typical values

40 V, 4.8 mOhm bi-directional Gallium Nitride (GaN) FET in a 2.1 mm x 2.1 mm Wafer Level Chip-Scale Package (WLCSP)



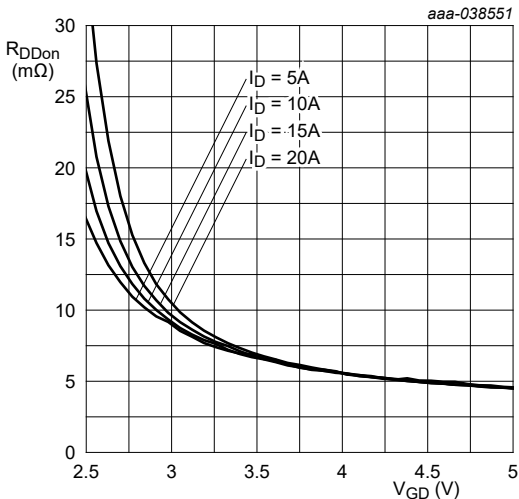
$I_D = 1\text{ mA}$  ;  $V_{DD} = V_{GD}$

Fig. 8. Gate-drain threshold voltage as a function of junction temperature



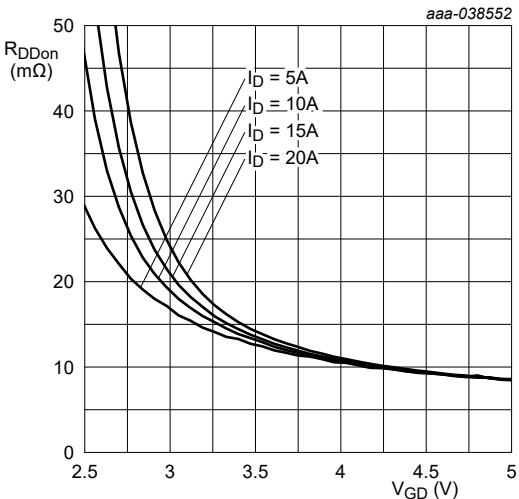
$$a = \frac{R_{DDon}}{R_{DDon}(25^\circ\text{C})}$$

Fig. 9. Normalized drain-drain on-state resistance factor as a function of junction temperature; typical values



$T_J = 25^\circ\text{C}$

Fig. 10. Drain-drain on-state resistance as a function of gate-drain voltage; typical values



$T_J = 125^\circ\text{C}$

Fig. 11. Drain-drain on-state resistance as a function of gate-drain voltage; typical values

40 V, 4.8 mOhm bi-directional Gallium Nitride (GaN) FET in a 2.1 mm x 2.1 mm Wafer Level Chip-Scale Package (WLCSP)

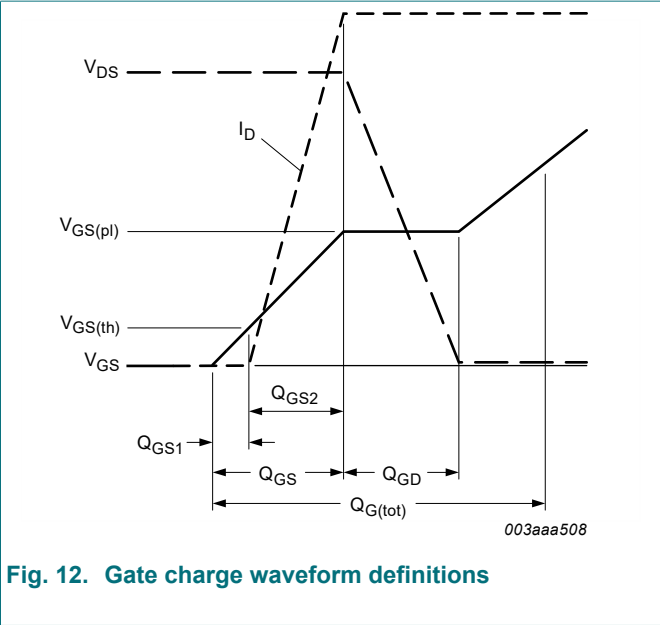


Fig. 12. Gate charge waveform definitions

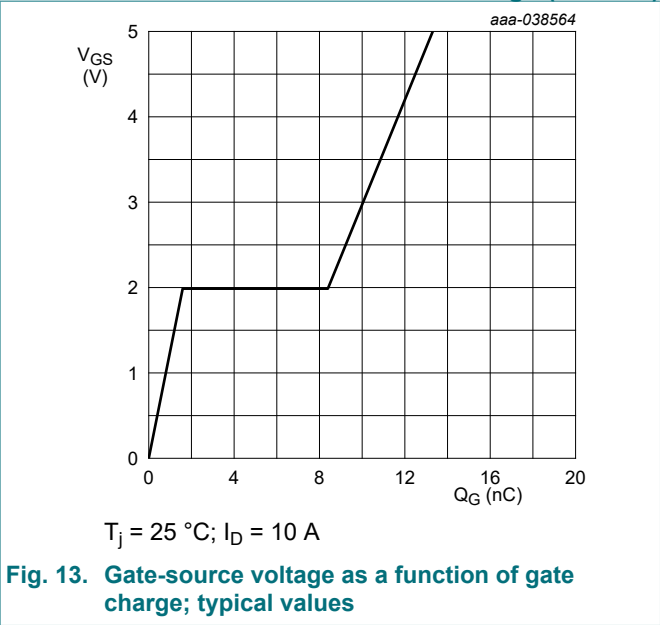


Fig. 13. Gate-source voltage as a function of gate charge; typical values

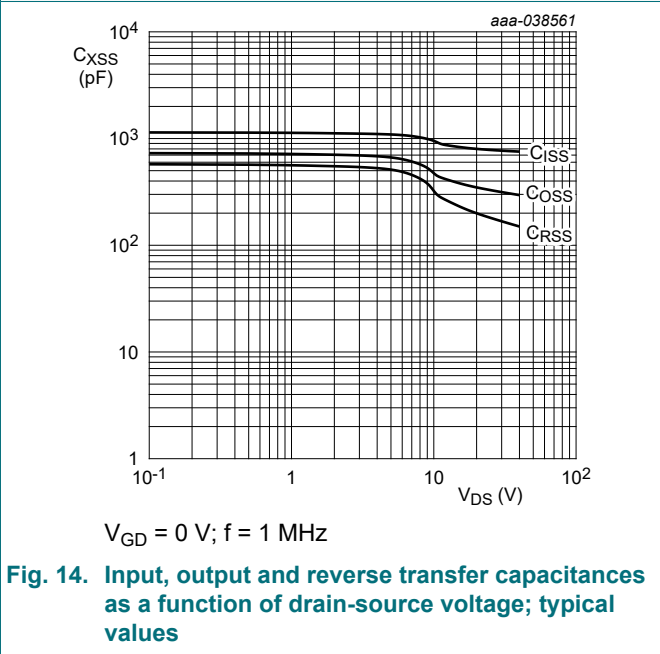


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

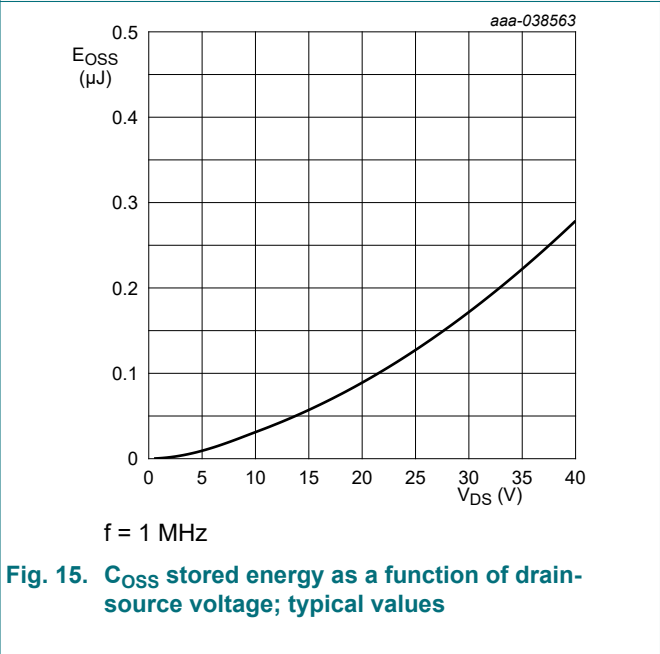
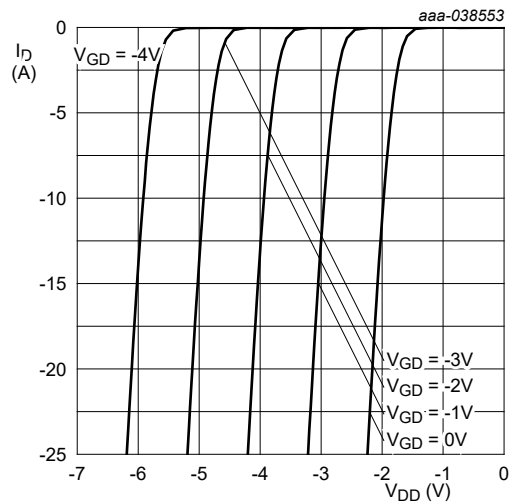


Fig. 15.  $C_{OSS}$  stored energy as a function of drain-source voltage; typical values

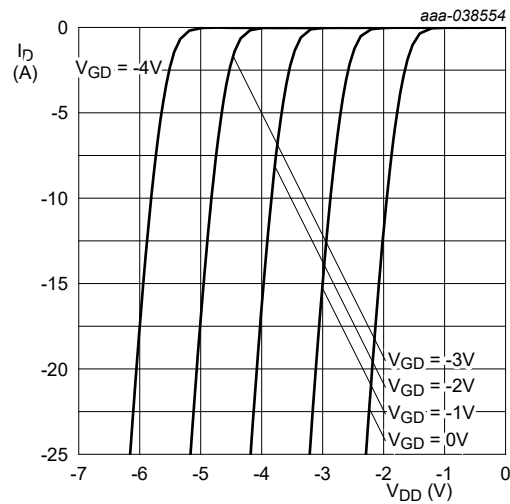


40 V, 4.8 mOhm bi-directional Gallium Nitride (GaN) FET in a 2.1 mm x 2.1 mm Wafer Level Chip-Scale Package (WLCSP)



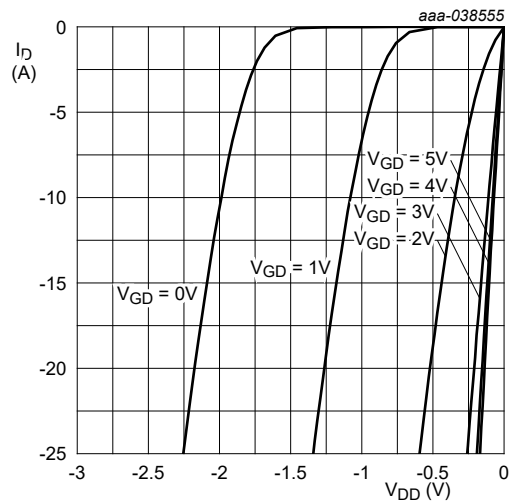
T<sub>j</sub> = 25 °C

Fig. 16. Reverse drain current as a function of drain-drain voltage; typical values



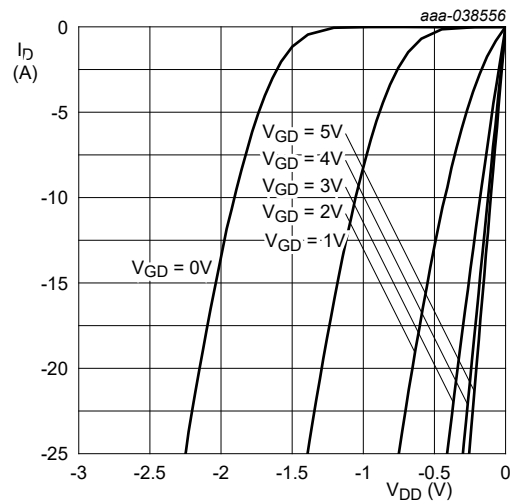
T<sub>j</sub> = 125 °C

Fig. 17. Reverse drain current as a function of drain-drain voltage; typical values



T<sub>j</sub> = 25 °C

Fig. 18. Reverse drain current as a function of drain-drain voltage; typical values



T<sub>j</sub> = 125 °C

Fig. 19. Reverse drain current as a function of drain-drain voltage; typical values

11. Package outline

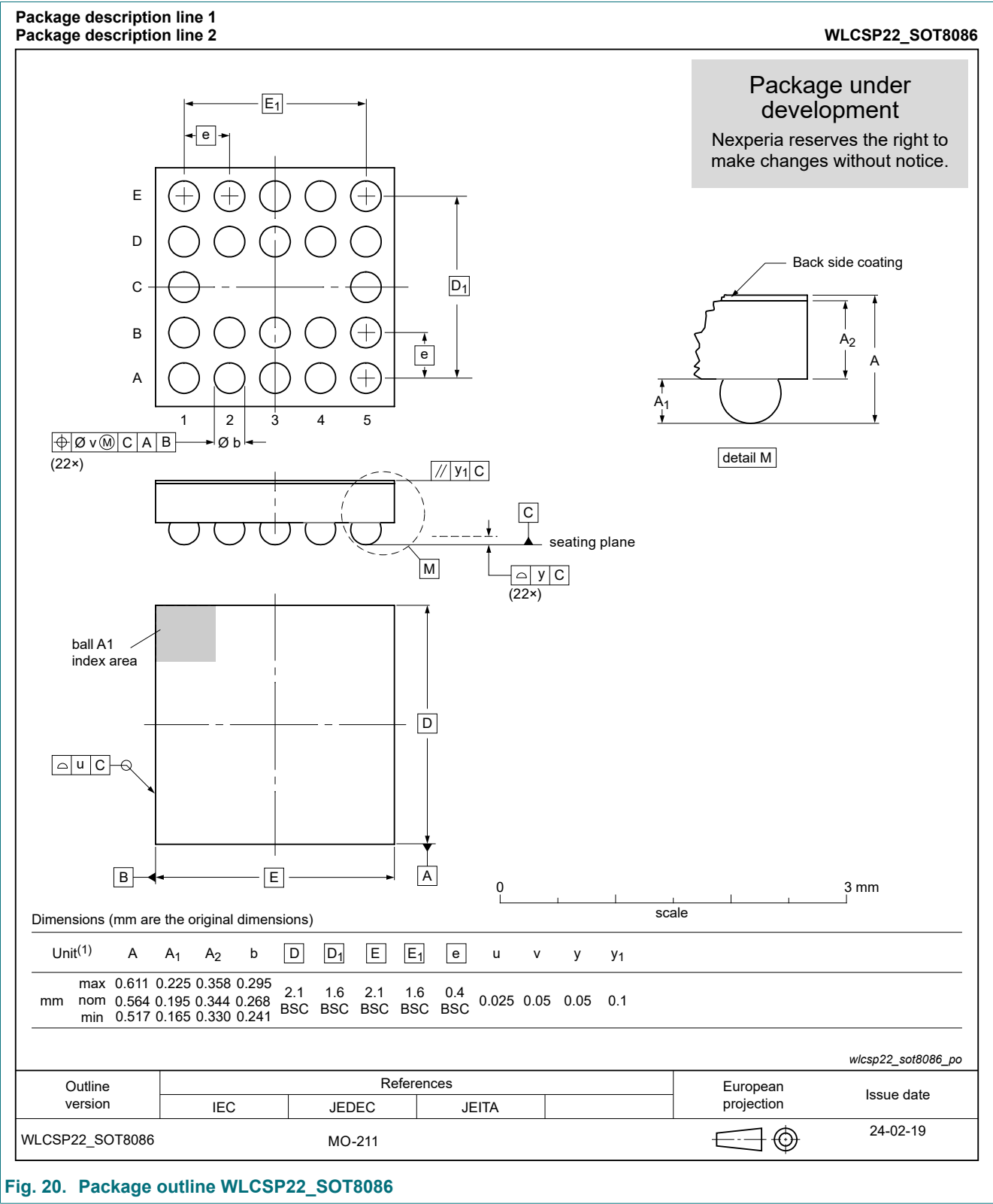
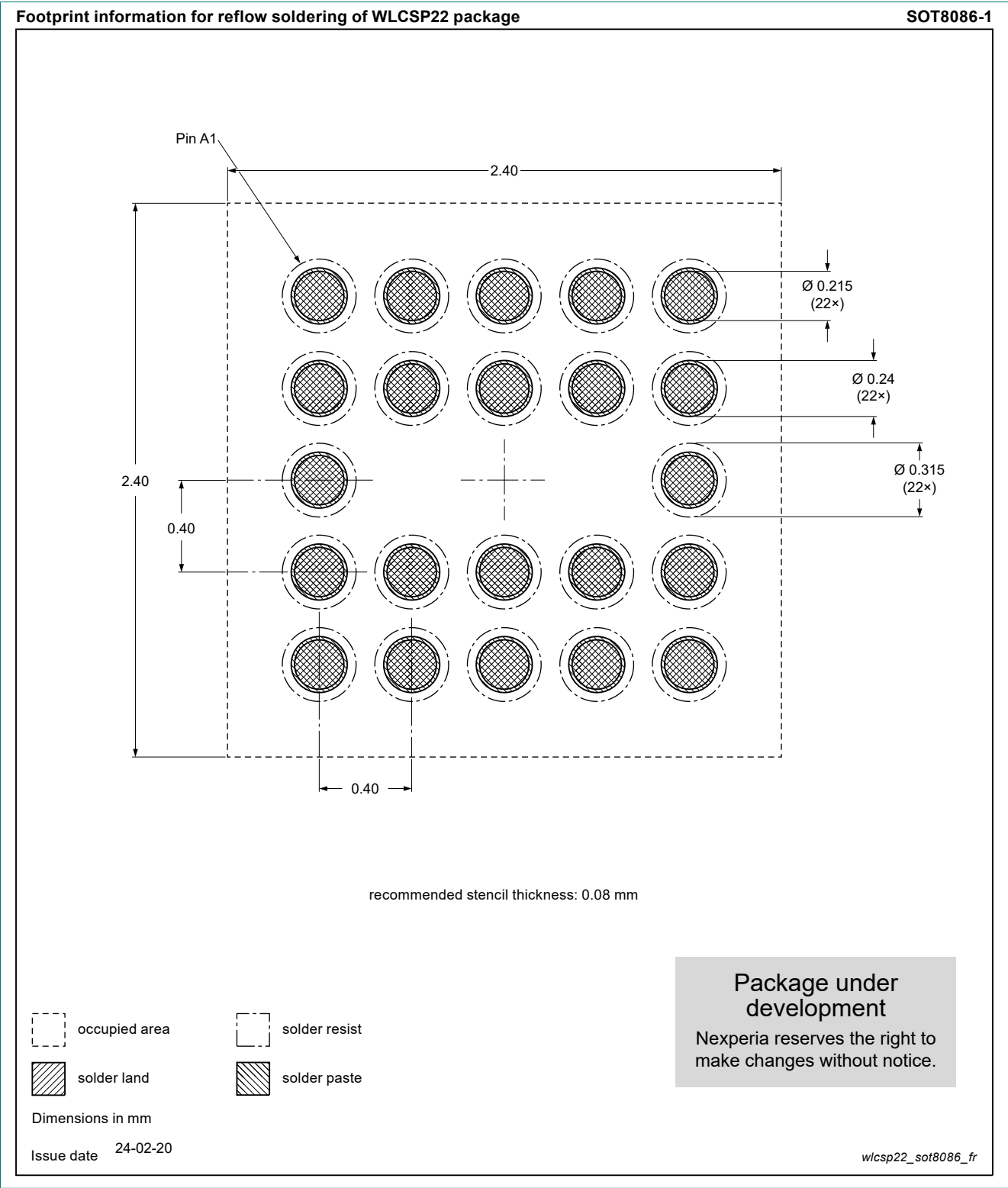


Fig. 20. Package outline WLCSP22\_SOT8086

12. Soldering



### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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